

LISTING OF THE CLAIMS:

This listing of the claims will replace all prior versions, and listings, of claims in the application:

Claim 1 (Currently Amended) An interconnect structure comprising:

one or more interconnect levels, one on top of each other, each level comprising an organo-silicate glass (OSG) dielectric material having a plasma treated surface layer that provides improved adhesion to an overlying lower hardmask, yet is substantially undamaged.

Claim 2 (Original) The interconnect structure of Claim 1 wherein the OSG dielectric material comprises a non-porous or porous material having a dielectric constant less than 3.

Claim 3 (Cancelled)

Claim 4 (Original) The interconnect structure of Claim 1 wherein the OSG dielectric material comprises a material of Si, C, O and H and having a dielectric constant less than about 3.

Claim 5 (Original) The interconnect structure of Claim 4 wherein the OSG dielectric material comprises about 10 to about 40 atomic (at.) % Si, about 10 to about 40 at. % C, about 15 to about 45 at. % O, and about 20 to about 50 at. % H.

Claim 6 (Original) The interconnect structure of Claim 1 further comprising a dielectric cap layer beneath said OSG dielectric material.

Claim 7 (Original) The interconnect structure of Claim 1 wherein the lower hardmask comprises a dielectric material of Si, C, O and H and having a dielectric constant less than about 5.

Claim 8 (Cancelled)

Claim 9 (Original) The interconnect structure of Claim 1 wherein the adhesion improved by greater than 15%.

Claim 10 (Original) The interconnect structure of Claim 1 further comprising an upper hardmask located atop said lower hardmask.

Claim 11 (Original) The interconnect structure of Claim 10 wherein said lower hardmask does not include a densified surface layer.

Claims 12-19 (Cancelled)